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17EE34

**Third Semester B.E. Degree Examination, Jan./Feb. 2021**

## Analog Electronic Circuits

Time: 3 hrs.

Max. Marks: 100

**Note: Answer any FIVE full questions, choosing ONE full question from each module.**

### Module-1

- 1 a. For the clipper limit shown in Fig Q1(a). Find  $V_0$ , sketch the  $V_0$  waveform and also draw the transfer characteristics

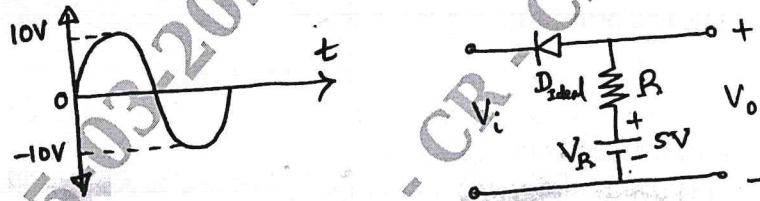


Fig Q1(a)

(07 Marks)

- b. With a neat circuit diagram, explain the operation fixed bias circuit. (07 Marks)
- c. What is biasing of a transistor? Explain the requirements of biasing circuits. (06 Marks)

### OR

- 2 a. Find the operating point for the voltage divider bias circuit with  $\beta = 80$  and  $V_{BE} = 0.6V$ . Find the new operating point when  $\beta$  changes to 100 and  $V_{BE}$  changes to 0.25V. Consider,  $V_{CC} = 15V$ ,  $R_1 = 100K\Omega$ ,  $R_2 = 18K\Omega$ ,  $R_c = 4.7K\Omega$  and  $R_E = 1K\Omega$ . (10 Marks)
- b. Obtain the expression for stability factor ( $S_{I_{CO}}$ ) for collector to base bias circuit. (05 Marks)
- c. Explain the operation of a transistor as a switch. (05 Marks)

### Module-2

- 3 a. Define h-parameters. Obtain the expression for current gain, voltage gain, input resistance and output resistance for CE configuration of BJT using h-parameters. (10 Marks)
- b. For the emitter follower circuit shown in Fig Q3(b). Calculate  $z_i$ ,  $z_o$ ,  $A_v$  and  $A_i$ . Take the h-parameter of the transistor to be  $h_{ie} = 1.1K\Omega$ ,  $h_{re} = 2.5 \times 10^{-4}$ ,  $h_{fe} = 50$ ,  $h_{oe} = 24 \mu A/v$

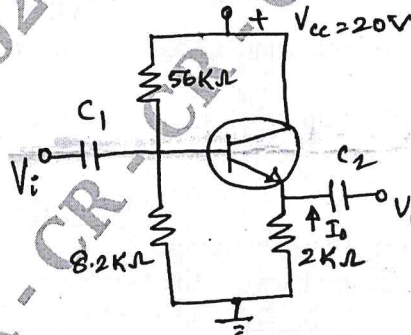


Fig Q3(b)

(06 Marks)

- c. A transistor in CE mode has h-parameters,  $h_{ie} = 1100\Omega$ ,  $h_{re} = 2.5 \times 10^{-4}$ ,  $h_{fe} = 99$  and  $h_{oe} = 25\mu A/v$ . Determine equivalent CB parameters. (04 Marks)

Important Note : 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.  
2. Any revealing of identification, appeal to evaluator and /or equations written eg, 42+8 = 50, will be treated as malpractice.

OR

- 4 a. For the common base circuit shown in Fig Q4(a), the transistor parameters are  $h_{ib} = 22\Omega$ ,  $h_{rb} = 2.9 \times 10^{-4}$ ,  $h_{fb} = -0.98$  and  $h_{ob} = 0.49 \mu\text{A/v}$ . Calculate the values of the input resistance, output resistance, current gain and voltage gain for the given circuit.

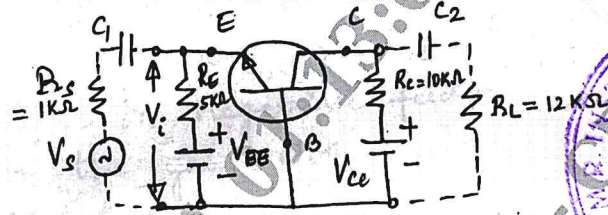


Fig Q4(a)

- b. State and prove Miller's theorem.

(10 Marks)

(10 Marks)

**Module-3**

- 5 a. Explain the need for cascading amplifier. Draw and explain block diagram of n-stage cascaded amplifier. (06 Marks)
- b. Compare the different types coupling methods used in multistage amplifiers. (08 Marks)
- c. With the help of a neat circuit diagram, explain the working of a Darlington emitter follower. (06 Marks)

OR

- 6 a. Define Negative and Positive feedback. With the help of block diagram, explain the concept of feedback amplifier. (07 Marks)
- b. Derive the expression for  $Z_{if}$  and  $Z_{of}$  for a voltage series feedback amplifier. (08 Marks)
- c. An amplifier having a voltage gain of 60dB uses  $1/20^{\text{th}}$  of its output in negative feedback. Calculate the gain with feedback, the percentage change in gain without and with feedback consequent on 50% change in  $g_m$  (transfer or mutual conductance). (05 Marks)

**Module-4**

- 7 a. Explain the operation of a class-B push pull power amplifier. Prove that the maximum efficiency of a class-B configuration is 78.5%. (10 Marks)
- b. State and explain Barkhausen criterion for sustained Oscillations. (05 Marks)
- c. Explain the features of power amplifiers. (05 Marks)

OR

- 8 a. Draw the circuit of Wein bridge oscillator and derive an expression for frequency of oscillator. (10 Marks)
- b. Explain the operation of class A transformer coupled power amplifier and prove that the maximum efficiency is 50%. (10 Marks)

**Module-5**

- 9 a. Discuss the construction, working and characteristics of an n-channel JFET. (10 Marks)
- b. Give the comparison between the following :  
i) BJT and FET    ii) JFET and MOSFET    iii) D-MOSFET and E-MOSFET. (10 Marks)

OR

- 10 a. Discuss the construction, working and characteristics of an enhancement type MOSFET [E-MOSFET]. (10 Marks)
- b. With necessary equivalent circuit, obtain the expression for voltage gain, input impedance and output impedance of a Fixed biased common source – JFET amplifier. (10 Marks)

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